



Product Summary

BV _{DSS}	Rds(on) max	Ι _D T _C = +25°C
-40V	$11m\Omega @ V_{GS} = -10V$	-74A
	19mΩ @ V_{GS} = -4.5V	-55A

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- DC-DC Converters
- Power Management Functions
- Backlighting

P-CHANNEL ENHANCEMENT MODE MOSFET

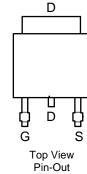
Features and Benefits

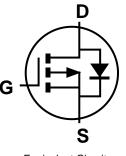
- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- An Automotive-Compliant Part is Available Under Separate Datasheet (<u>DMP4011SK3Q</u>)

Mechanical Data

- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.33 grams (Approximate)







Equivalent Circuit

Ordering Information (Note 4)

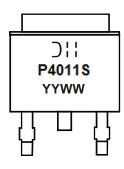
Part Number	Case	Packaging
DMP4011SK3-13	TO252 (DPAK)	2,500/Tape & Reel

Notes: 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and

Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



Dif = Manufacturer's Marking P4011S = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 19 = 2019) WW = Week (01 to 53)



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit				
Drain-Source Voltage	V _{DSS}	-40	V				
Gate-Source Voltage			V _{GSS}	±20	V		
Continuous Dusin Current (Nata C) // 40//	Steady State	$T_{C} = +25^{\circ}C$ $T_{C} = +70^{\circ}C$	ID	-74 -59	A		
Continuous Drain Current (Note 6) V _{GS} = -10V	Steady State	T _A = +25°C T _A = +70°C	I _D	-14 -11	А		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	-200	A		
Maximum Body Diode Forward Current (Note 6)			Is	-70	A		
Pulsed Source Current (10µs Pulse, Duty Cycle = 1%)			Pulsed Source Current (10µs Pulse, Duty Cycle = 1%)		I _{SM}	-200	A
Avalanche Current, L = 1mH (Note 7)			I _{AS}	-22	A		
Avalanche Energy, L = 1mH (Note 7)			E _{AS}	250	mJ		

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		PD	1.8	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	84	°C/W
Total Power Dissipation (Note 6)		PD	3.1	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	41	°C/W
Thermal Resistance, Junction to Case		$R_{\theta JC}$	1.4	C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)			•			÷	
Drain-Source Breakdown Voltage	BV _{DSS}	-40		—	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	—		-1	μA	$V_{DS} = -32V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS	_		±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)			-				
Gate Threshold Voltage	V _{GS(TH)}	-1.0	-2.0	-2.5	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$	
Static Drain-Source On-Resistance	Passa	_	6.5	11	mΩ	$V_{GS} = -10V, I_D = -9.8A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	—	10.8	19	1115.2	$V_{GS} = -4.5V, I_D = -9.8A$	
Diode Forward Voltage	V _{SD}	_	-0.7	-1	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss	—	2747	—		$V_{DS} = -20V, V_{GS} = 0V$ f = 1MHz	
Output Capacitance	C _{oss}	_	508	—	pF		
Reverse Transfer Capacitance	C _{rss}	—	222	—			
Gate Resistance	Rg	_	21.4	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Qg	_	25	_		V _{DS} = -20V, I _D = -9.8A	
Total Gate Charge (V _{GS} = -10V)	Qg	_	52	_	nC		
Gate-Source Charge	Q _{gs}	_	8.5	—	nc		
Gate-Drain Charge	Q _{gd}	_	11.8	_			
Turn-On Delay Time	t _{D(ON)}		6.6	_		$V_{GS} = -10V, V_{DD} = -20V,$ $R_G = 6\Omega, I_D = -1A$	
Turn-On Rise Time	t _R		6.5	_			
Turn-Off Delay Time	t _{D(OFF)}	_	222	_	ns		
Turn-Off Fall Time	t _F		138	_			
Reverse Recovery Time	t _{RR}	_	25	_	ns	I _F = -9.8A, di/dt = -100A/µs	
Reverse Recovery Charge	Q _{RR}	_	17		nC	I _F = -9.8A, di/dt = -100A/µs	

 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. Notes:

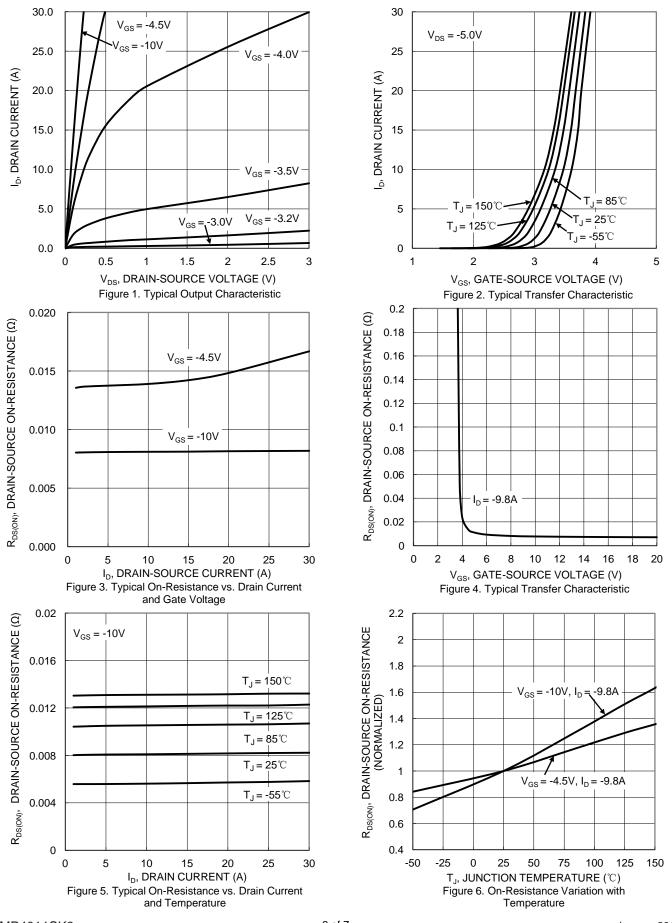
7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.

8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to product testing.



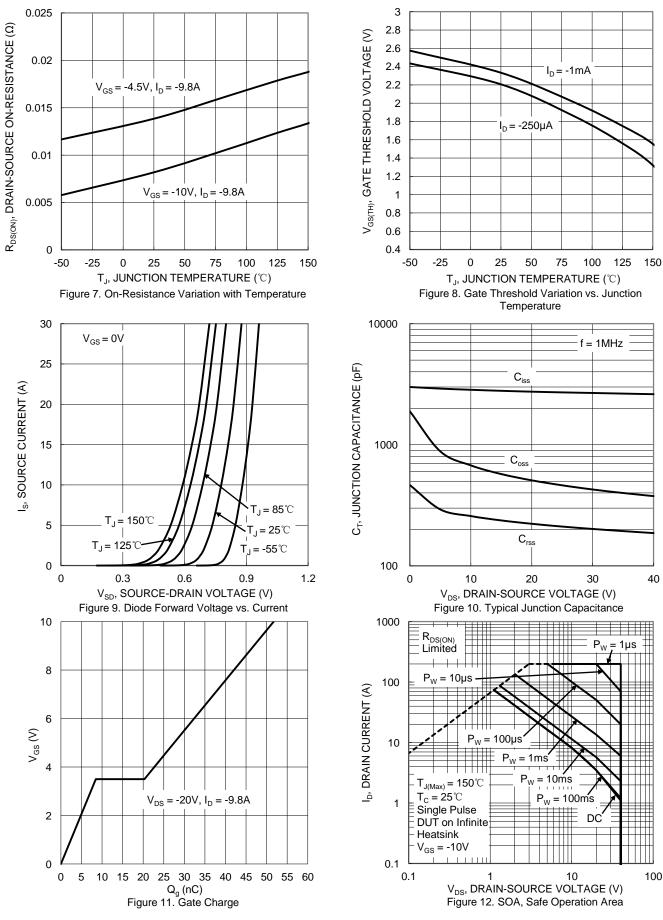
DMP4011SK3



DMP4011SK3 Document number: DS40926 Rev. 2 - 2

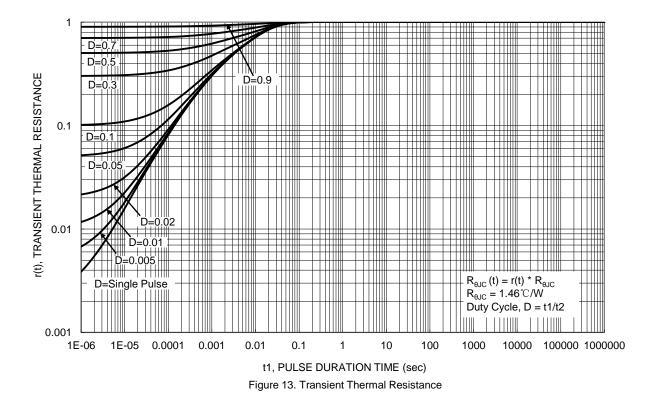


DMP4011SK3



DMP4011SK3 Document number: DS40926 Rev. 2 - 2 January 2019 © Diodes Incorporated



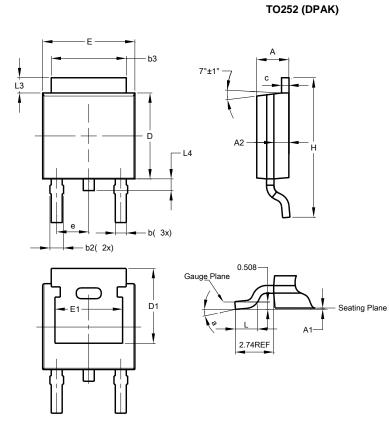


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Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

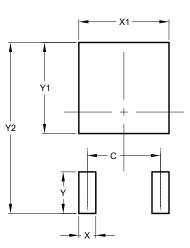


TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
С	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
Ε	6.45	6.70	6.58		
E1	4.32	-	-		
Н	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All	All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)
С	4.572
Х	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700



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